

CMS35P06D-HF

P-Channel
RoHS Device
Halogen Free



Features

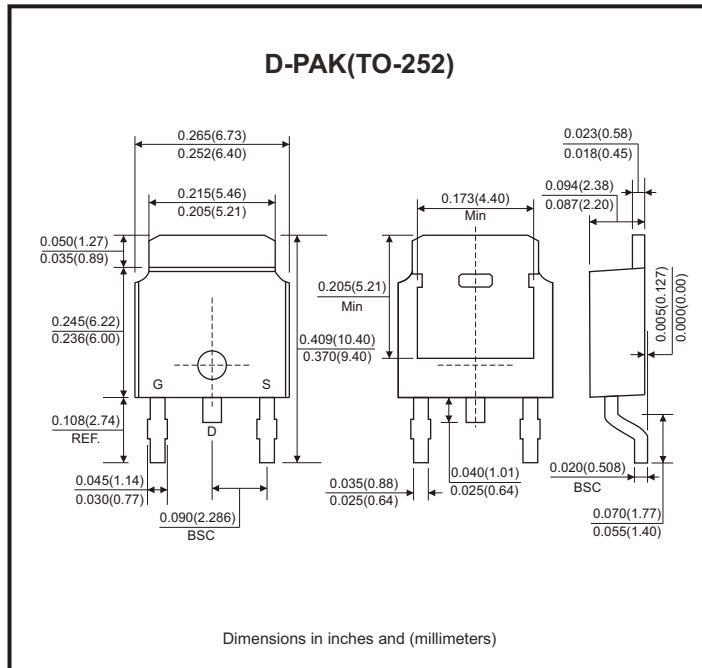
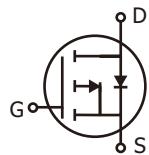
- Advanced DMOS trench technology.
- Fast switching.
- Green device available.
- 100% EAS guaranteed.

Mechanical data

- Case: D-PAK/TO-252 standard package, molded plastic.

Circuit Diagram

- G : Gate
- S : Source
- D : Drain



Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
Drain-source voltage		V _{DS}	-60	V
Gate-source voltage		V _{GS}	±20	V
Continuous drain current (Note 1)	I _D @ T _c = 25°C		-35	A
	I _D @ T _c = 100°C		-22.1	
Pulsed drain current (Note 1, 2)		I _{DM}	-140	A
Total power dissipation (Note 4)	P _D @ T _c = 25°C		72.6	W
	P _D @ T _A = 25°C		2	
Single pulse avalanche energy, L=0.1mH (Note 3)		E _{AS}	80	mJ
Single pulse avalanche current, L=0.1mH (Note 3)		I _{AS}	-40	A
Operating junction and storage temperature range		T _J , T _{STG}	-55 to +150	°C
Thermal resistance junction-ambient (Note 1)	Steady state	R _{θJA}	62.5	°C/W
Thermal resistance junction-case (Note 1)	Steady state	R _{θJC}	1.72	°C/W

Electrical Characteristics (at $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-60			V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-1.0	-1.4	-2.5	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Drain-source leakage current ($T_J=25^\circ\text{C}$)	I_{DSS}	$V_{\text{DS}} = -60\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Drain-source leakage current ($T_J=125^\circ\text{C}$)		$V_{\text{DS}} = -48\text{V}, V_{\text{GS}} = 0\text{V}$			-10	
Static drain-source on-resistance (Note 2)	$R_{\text{DS(on)}}$	$V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -20\text{A}$		23	28	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -10\text{A}$		28	35	
Total gate charge (Note 2)	Q_g	$I_{\text{D}} = -5\text{A}, V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = -10\text{V}$		43.8		nC
Gate-source charge	Q_{gs}			4.6		
Gate-drain ("miller") charge	Q_{gd}			8.3		
Turn-on delay time (Note 2)	$t_{\text{d(on)}}$	$V_{\text{DD}} = -30\text{V}, V_{\text{GS}} = -10\text{V}$ $I_{\text{D}} = -1\text{A}, R_{\text{G}} = 6\Omega$		25		nS
Rise time	t_r			13.8		
Turn-off delay time	$t_{\text{d(off)}}$			148		
Fall time	t_f			51		
Input capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = -25\text{V}, f = 1\text{MHz}$		2595		pF
Output capacitance	C_{oss}			162		
Reverse transfer capacitance	C_{rss}			115		
Source-drain diode						
Diode forward voltage (Note 2)	V_{SD}	$I_{\text{S}} = -20\text{A}, V_{\text{GS}} = 0\text{V}, T_J=25^\circ\text{C}$			-1.2	V
Continuous source current (Note 1, 6)	I_{S}	$V_G = V_D = 0\text{V}$, Force current			-35	A
Pulsed source current (Note 2, 6)	I_{SM}				-70	A
Guaranteed avalanche characteristics						
Single pulse avalanche energy (Note 5)	E_{AS}	$V_{\text{DD}} = -25\text{V}, L=0.1\text{mH}, I_{\text{AS}} = -20\text{A}$	20			mJ

- Notes:
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2 oz copper.
 2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
 3. The EAS data shows max. rating. The test condition is $V_{\text{DD}}=-25\text{V}, V_{\text{GS}}=-10\text{V}, L=0.1\text{mH}, I_{\text{AS}}=-40\text{A}$.
 4. The power dissipation is limited by 150°C junction temperature.
 5. The min. value is 100% EAS tested guarantee.
 6. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

Rating and Characteristic Curves (CMS35P06D-HF)

Fig.1 - Drain Current vs. T_c

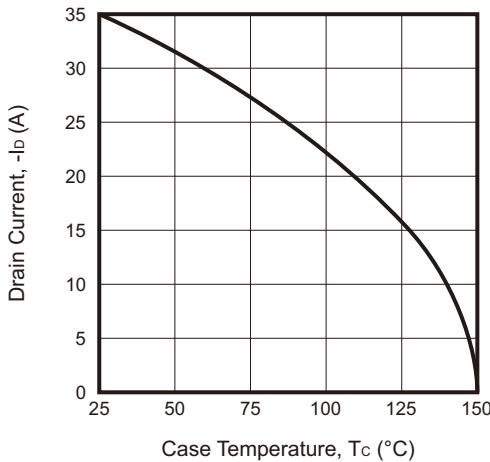


Fig.2 - Gate Charge Characteristics

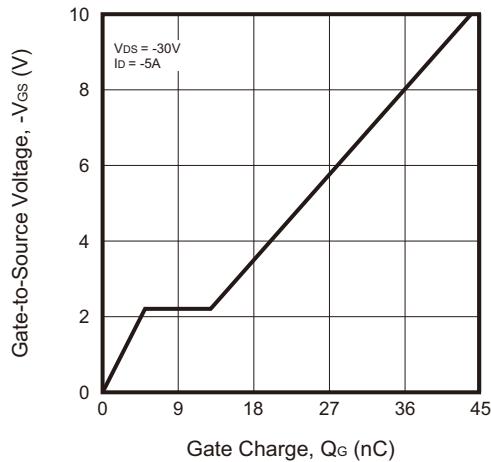


Fig.3 - Normalized $V_{GS(th)}$ vs. T_J

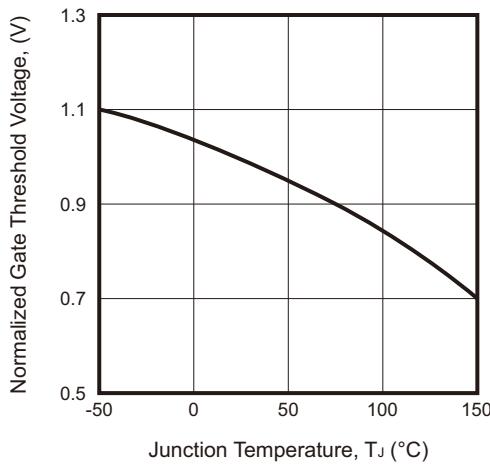


Fig.4 - Normalized $R_{DS(ON)}$ vs. T_J

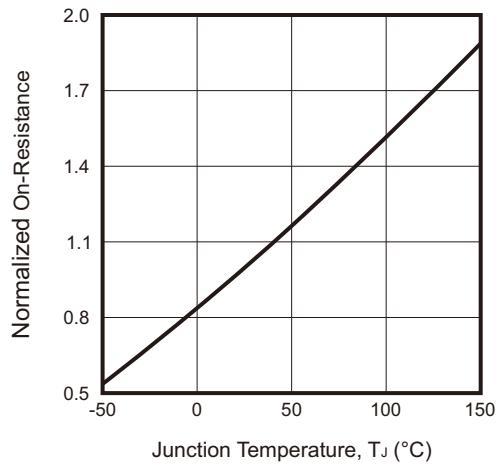
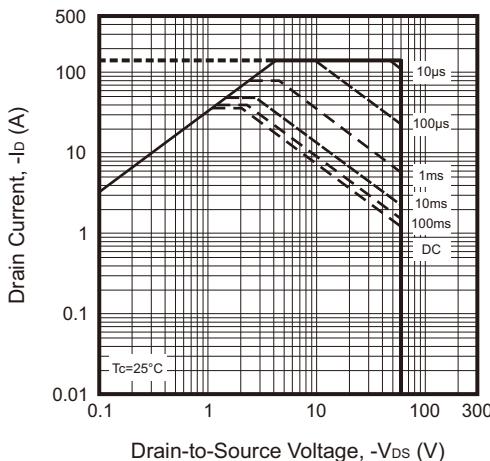
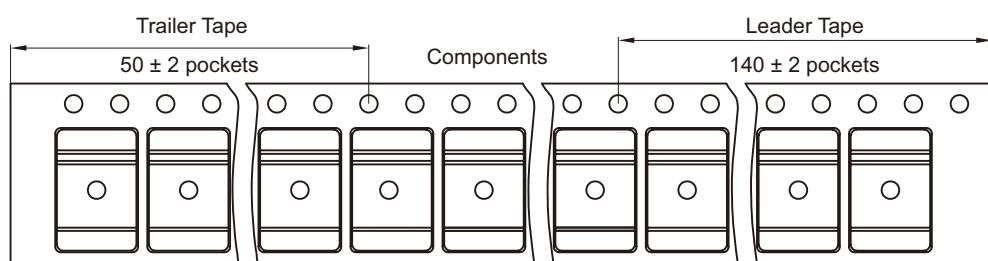
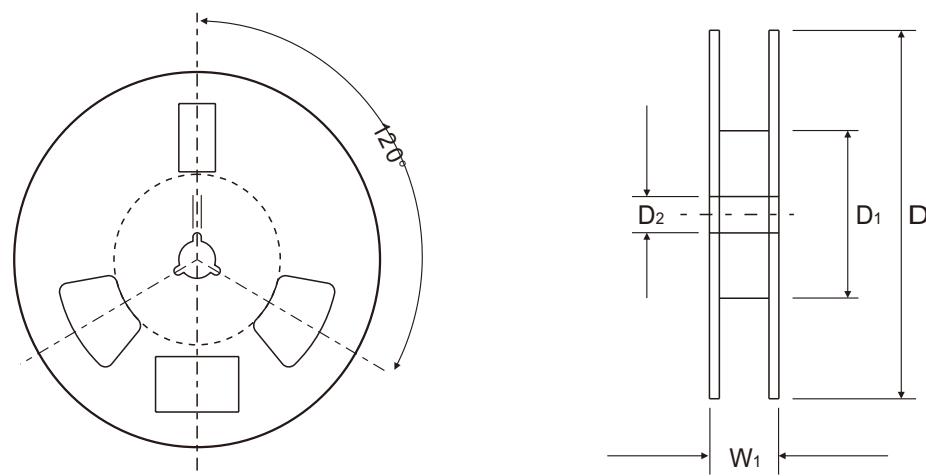
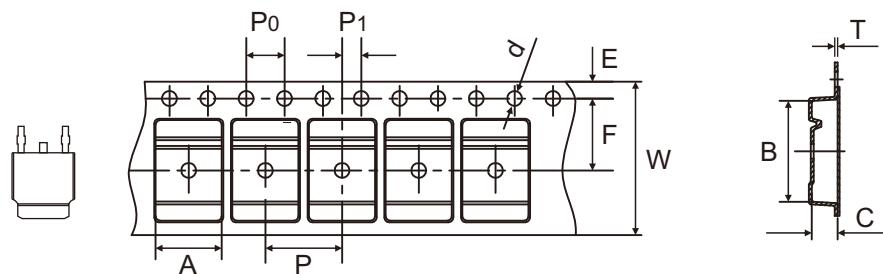


Fig.5 - Safe Operating Area



Company reserves the right to improve product design , functions and reliability without notice.

Reel Taping Specification



TO-252 (D-PAK)	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	1.55 ± 0.05	332 Max	100.00 ± 2.00	13.00 Min
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.106 ± 0.004	0.061 ± 0.002	13.071 Max	3.937 ± 0.079	0.512 Min

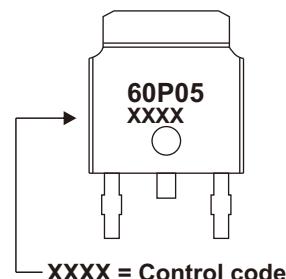
TO-252 (D-PAK)	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05	16.00 ± 0.10	22.4 Max
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.012 ± 0.002	0.630 ± 0.004	0.882 Max

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REV:A

Marking Code

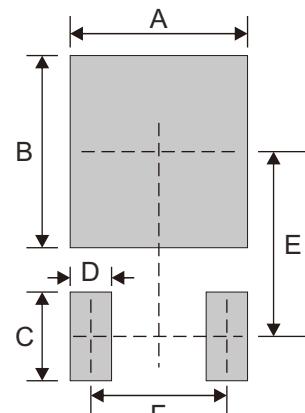
Part Number	Marking Code
CMS35P06D-HF	60P05



XXXX = Control code

Suggested PAD Layout

SIZE	TO-252/D-PAK	
	(mm)	(inch)
A	6.00	0.236
B	6.50	0.256
C	3.00	0.118
D	1.40	0.055
E	6.25	0.246
F	4.60	0.181



Note: 1. The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
TO-252/D-PAK	3,000	13